

Form PTO-1449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

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Applicant

Shigetoshi ITO and Yuhzoh TSUDA

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Group Art Unit Not Yet Assigned *2822*

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## U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
<i>[Signature]</i>	1.	04/25/2002	2002/0048302	Kimura			
	2.	05/16/2002	2002/0056836	Sawazaki et al.			
	3.	07/04/2002	2002/0084452	Ota et al.			
	4.	07/04/2002	2002/0085603	Okumura			
	5.	02/03/1998	5,714,772	Fang et al.			
	6.	04/14/1998	5,739,554	Edmond et al.			
	7.	01/09/2001	6,172,382	Nagahama et al.			
	8.	05/15/2001	6,232,623	Morita			
<i>[Signature]</i>	9.	12/11/2001	6,329,667	Ota et al.			

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO
<i>[Signature]</i>	10.	01/26/1998	11-214788	Japan			

## OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
<i>[Signature]</i>	11.	Kuramoto et al. (1999) "Room-Temperature Continuous-Wave Operation of InGaN Multi-Quantum-Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact," <i>Jpn. J. Appl. Phys.</i> 38: L184-186.
<i>[Signature]</i>	12.	Nakamura et al. (1998) "InGaN/GaN/AlGaIn-Based Laser Diodes Grown on GaN Substrates with a Fundamental Transverse Mode," <i>Jpn. J. Appl. Phys.</i> 37: L1020-1022.

EXAMINER: *[Signature]*DATE CONSIDERED: *7-17-04*

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.